ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE2536 (NPN) & NTE2537 (PNP)
Silicon Complementary Transistors
High Current Switch

Features:
- High Current Capacity
- Wide ASO Range
- Low Saturation Voltage

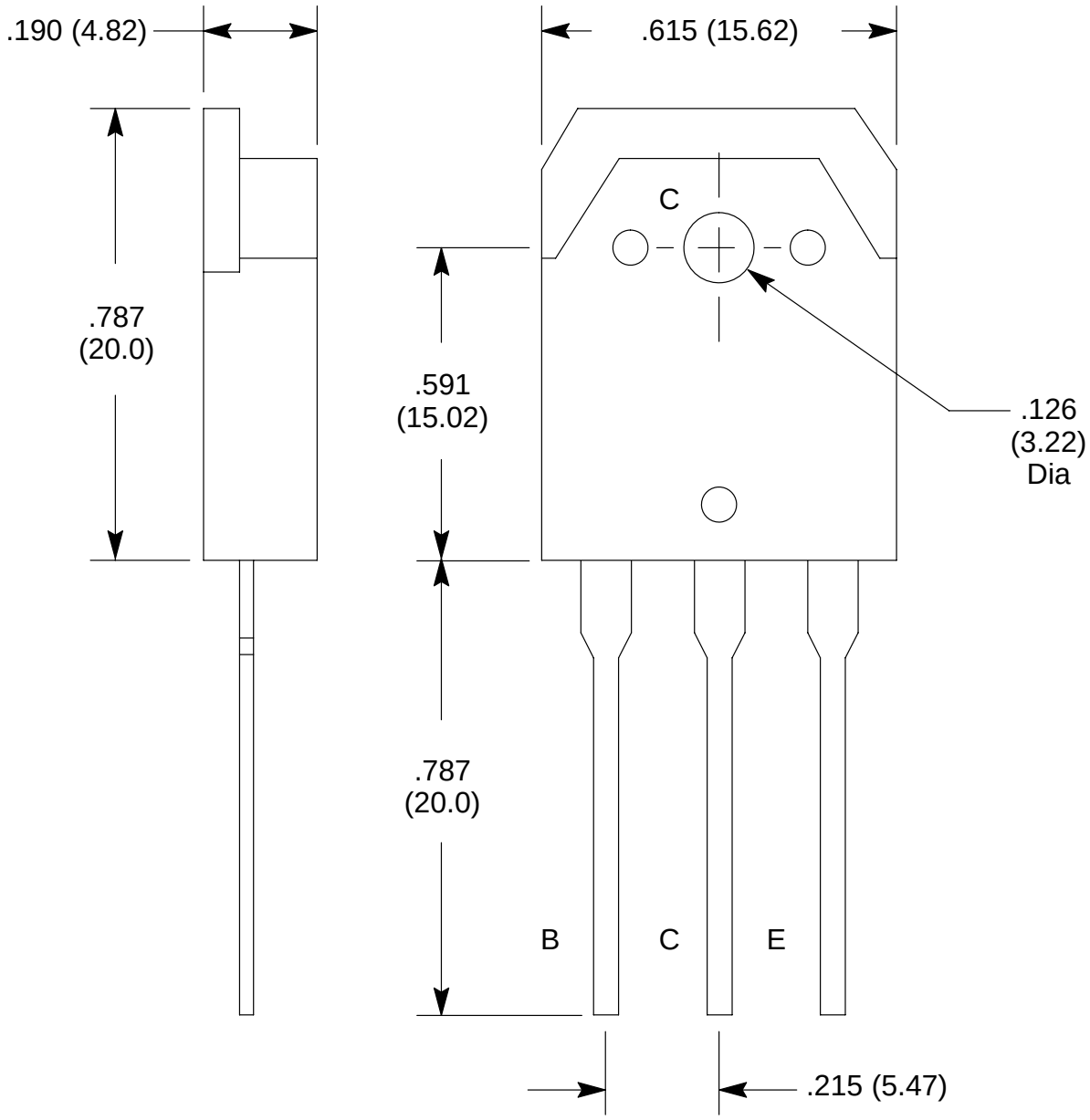
Applications:
- Motor Drivers
- Relay Drivers
- Converters

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector Base Voltage, V_{CBO} 110V
Collector Emitter Voltage, V_{CEO} 100V
Emitter Base Voltage, V_{EBO} 6V
Collector Current, I_C
  Continuous 40A
  Peak 65A
Base Current, I_B 12A
Collector Power Dissipation (T_C = +25°C), P_C 150W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 100V, I_E = 0	–	–	0.1	mA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0	–	–	0.1	mA
DC Current Gain	h_{FE}	V_{CE} = 2V, I_C = 4A	50	–	140	
		V_{CE} = 2V, I_C = 16A	20	–	–	
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 16A, I_B = 1.6A	–	–	0.8	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 16A, I_B = 1.6A	–	–	1.5	V
Collector Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 1mA, I_E = 0	110	–	–	V
Collector Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 5mA, R_{BE} = ∞	100	–	–	V
Emitter Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 1mA, I_C = 0	6	–	–	V


.190 (4.82)
.615 (15.62)
C
.787
(20.0)
.591
(15.02)
.126
(3.22)
Dia
.787
(20.0)
B
C
E
.215 (5.47)